

Features

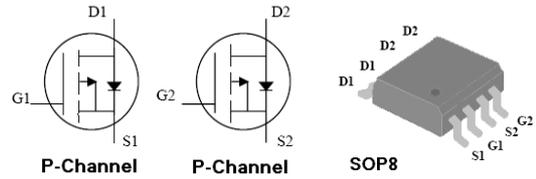
- Low $R_{DS(on)}$ @ $V_{GS}=-5V$
- 5V Logic Level Control
- Dual P-Channel SOP8 Package
- Pb-Free, RoHS Compliant

Key Items	PMOS	Unit
BVDSS	-30	V
ID	-5.8	A
$R_{DS(on)}$ @ $V_{GS}=-4.5V$	50	mΩ
$R_{DS(on)}$ @ $v_{GS}=-2.5V$	70	mΩ

Applications

The PTS4803 uses advanced trench technology to provide excellent RDS(ON) with low gate charge.

This device is suitable for use as a load switch or in PWM applications, optimized for Power Management applications for Portable Products, such as H-bridge, Inverters Car Charger and Others



Order Information

Product	Package	Marking	Packing	Min Unit Quantity
PTS4803	SOP8	PTS4803	3000PCS/Reel	3000PCS

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{GS}	Gate-Source Voltage	±12	V
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	-30	V
T_J	Maximum Junction Temperature	175	°C
T_{STG}	Storage Temperature Range	-50 to 150	°C
I_S	Diode Continuous Forward Current ^①	$T_C=25^\circ C$ -5.8	A
Mounted on Large Heat Sink			
I_{DM}	Pulse Drain Current Tested ^②	$T_C=25^\circ C$ -22	A
I_D	Continuous Drain Current($V_{GS}=10V$)	$T_C=25^\circ C$ -5.8	A
		$T_C=100^\circ C$ -5	
P_D	Maximum Power Dissipation	$T_C=25^\circ C$ 2	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	89	°C/W

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current ($T_C=25^\circ C$)	$V_{DS}=-30V, V_{GS}=0V$	--	--	1	μA
	Zero Gate Voltage Drain Current ($T_C=125^\circ C$)	$V_{DS}=-30V, V_{GS}=0V$	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 12V, V_{DS}=0V$	--	--	± 100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.6	-0.9	-1.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=-4.5V, I_D=-5A$	--	50	60	m Ω
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS}=-2.5V, I_D=-3A$	--	70	85	m Ω
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V,$ $f=1MHz$	--	480	--	pF
C_{oss}	Output Capacitance		--	90	--	pF
C_{rss}	Reverse Transfer Capacitance		--	50	--	pF
Q_g	Total Gate Charge	$V_{DS}=-15V, I_D=-3A,$ $V_{GS}=-4.5V$	--	12	--	nC
Q_{gs}	Gate-Source Charge		--	3.5	--	nC
Q_{gd}	Gate-Drain Charge		--	2.8	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-20V,$ $I_D=-6A,$ $R_G=3.3\Omega,$ $V_{GS}=-4.5V$	--	8	--	ns
t_r	Turn-on Rise Time		--	5	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	22	--	nS
t_f	Turn-Off Fall Time		--	8.5	--	nS
Source- Drain Diode Characteristics						
I_{SD}	Source-drain current(Body Diode)	$T_C=25^\circ C$	-3	--		A
V_{SD}	Forward on voltage	$T_j=25^\circ C, I_{SD}=-4A$ $V_{GS}=0V$	--	-0.8	-1.2	V

Notes:

- ① Pulse test ; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- ② Pulse width limited by maximum allowable junction temperature.

P-Channel Typical Characteristics

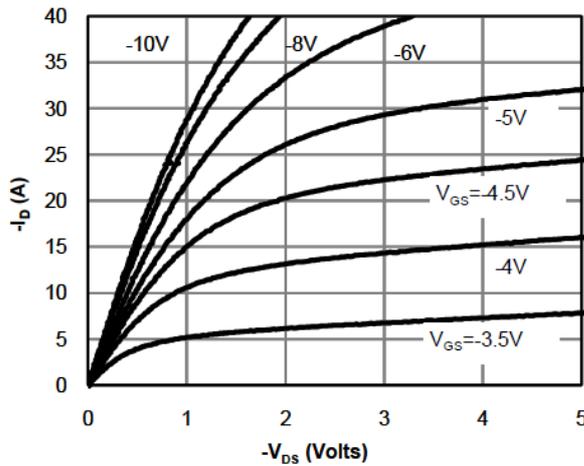


Fig 1: On-Region Characteristics

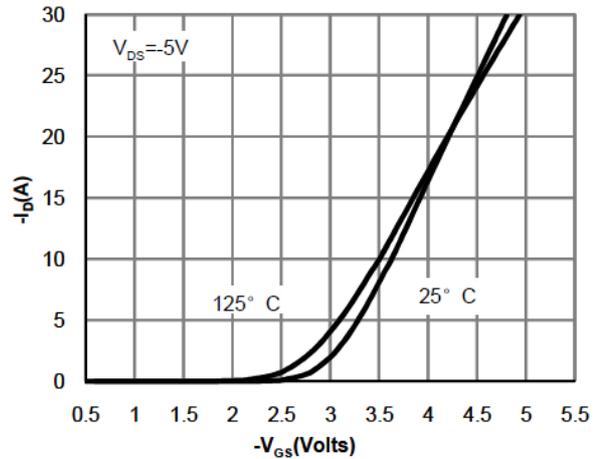


Figure 2: Transfer Characteristics

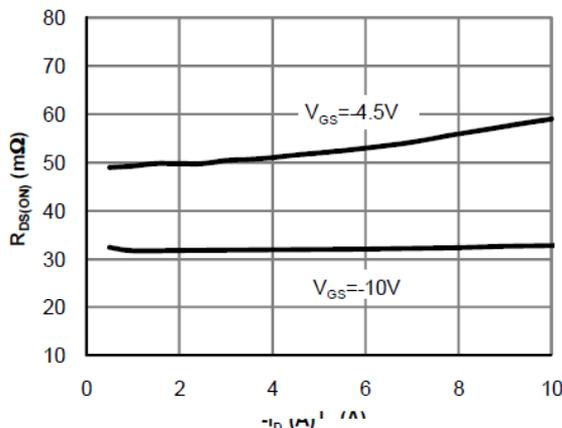


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

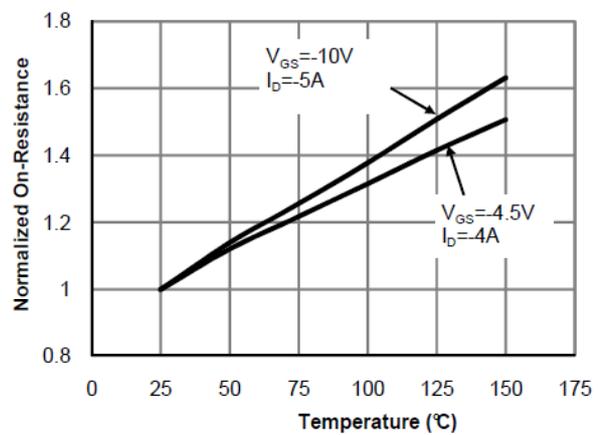


Figure 4: On-Resistance vs. Junction Temperature

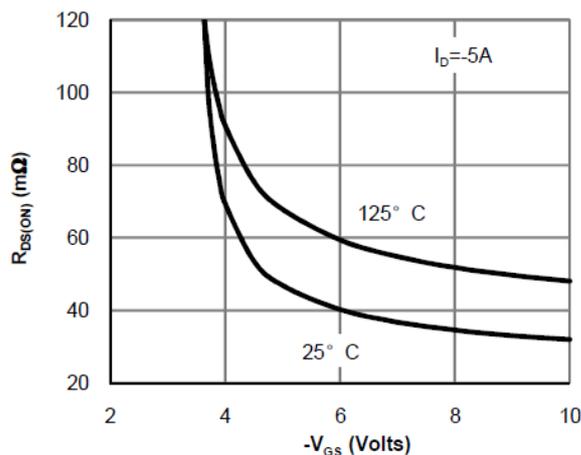


Figure 5: On-Resistance vs. Gate-Source Voltage

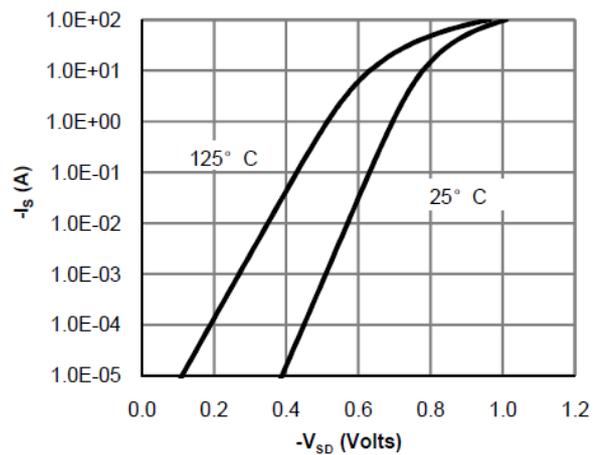


Figure 6: Body-Diode Characteristics

P-Channel Typical Characteristics

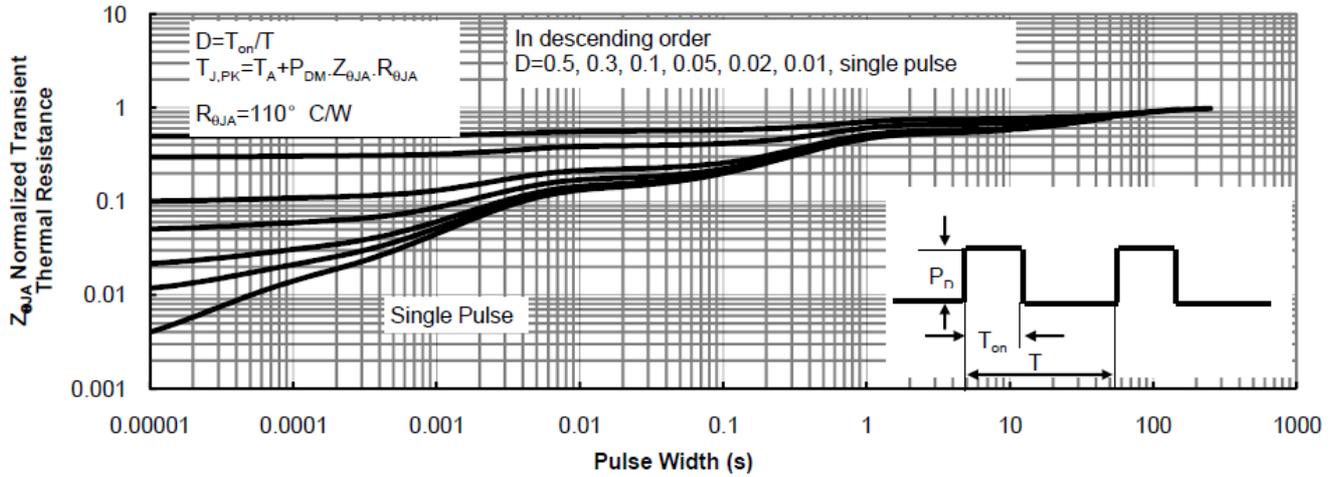


Figure 12: Normalized Maximum Transient Thermal Impedance

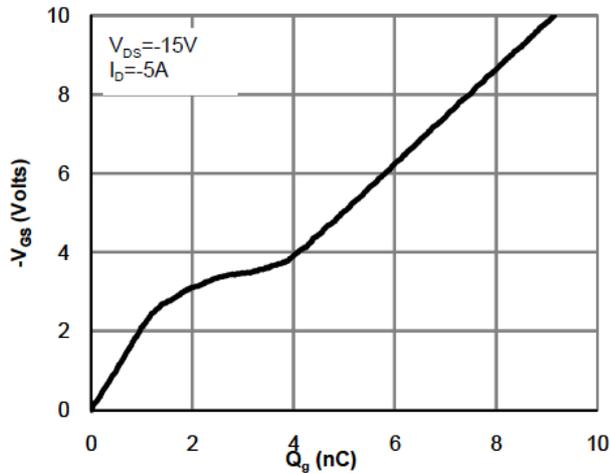


Figure 7: Gate-Charge Characteristics

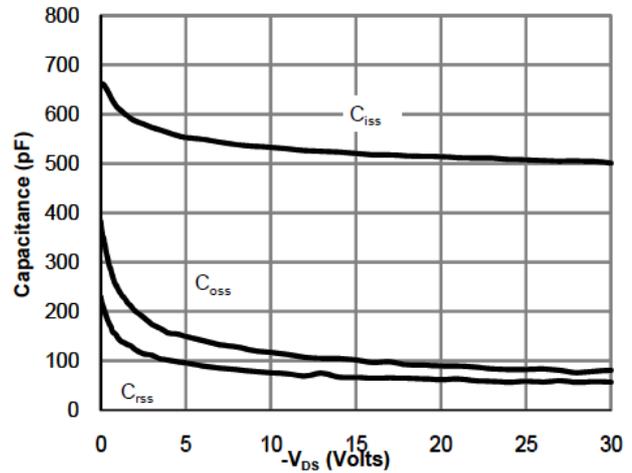


Figure 8: Capacitance Characteristics

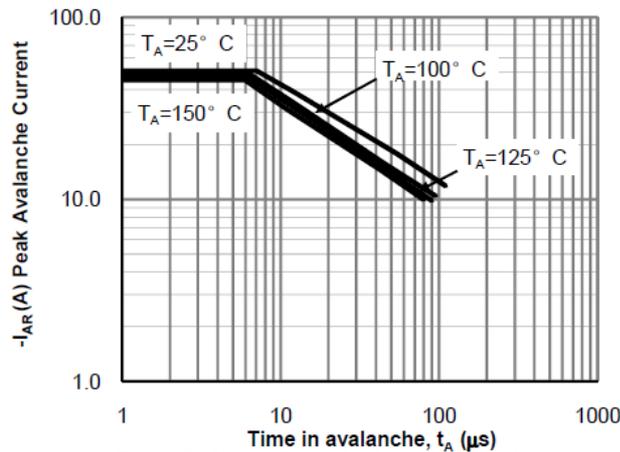


Figure 9: Single Pulse Avalanche capability

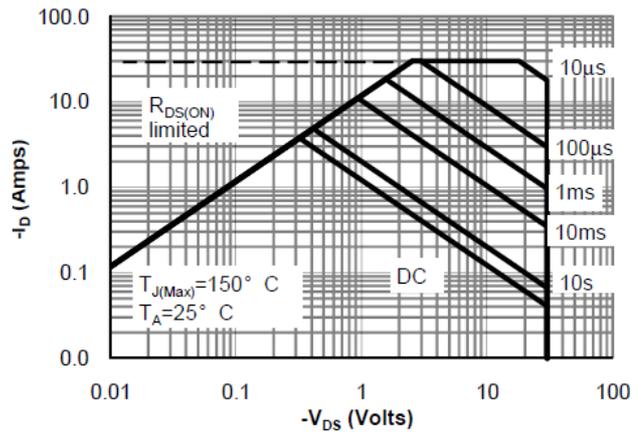
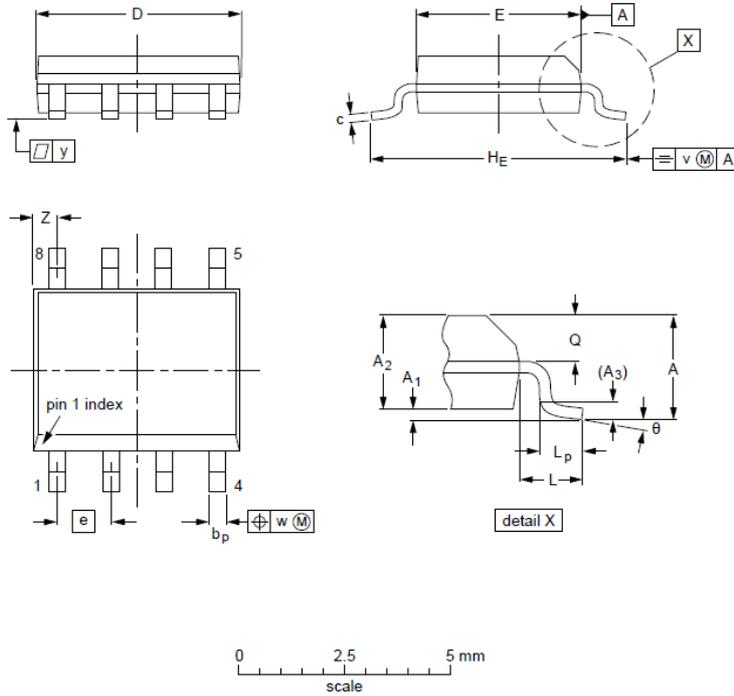


Figure 10: Maximum Forward Biased Safe Operating Area

Package Out Line Dimensions



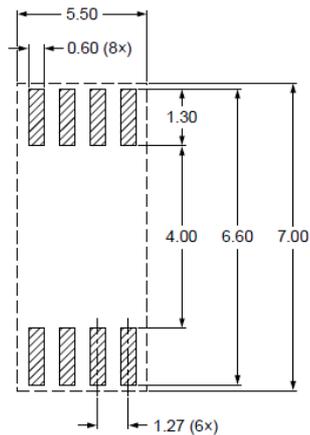
DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽²⁾	e	H _E	L	L _p	Q	v	w	y	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	5.0 4.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.20 0.19	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	

Notes

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

Reflow soldering footprint for SOP8



solder lands
 occupied area
 placement accuracy ± 0.25
 Dimensions in mm

Customer Service

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